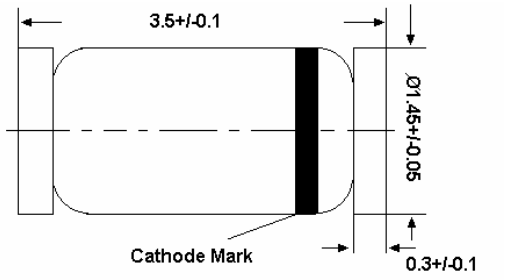
LL355

SWITECHING DIODE



Glass case MiniMELF
Dimensions in mm

Applications

- High speed switching

Features

- High Speed (tr = 1.2ns Typ.)
- High reliability with high surge current handling capability.

Construction

- Silicon epitaxial planar.

Absolute Maximum Ratings (T_a = 25^{O}C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	90	V
DC reverse voltage	V_R	80	V
Peak forward current	I_{FM}	225	mA
Mean rectifying current	I_o	100	mA
Surge current (1s)	I_{surge}	500	mA
Junction temperature	T_J	125	^{O}C
Storage temperature	T_{stg}	-55 to +125	^{O}C

Characteristics at T_a = 25 ^{O}C

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Forward voltage	V_F	-	-	1.2	V	I_F = 100mA
Reverse current	I_R	-	-	0.1	µA	V_R = 80V
Capacitance between terminals	C_T	-	-	3	pF	V_R = 0.5V, f = 1MHZ
Reverse recovery time	t_{rr}	-	-	4	ns	V_R = 6V, I_F = 10mA, R_L = 100Ω